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Supporting Information for

Alkaline-earth metal embedded expanded phthalocyanine nanosheets with direct band gap and high power conversion efficiency

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Table S13. Calculated band gap of the donor (E_g), conduction band offset (ΔE_c), open circuit voltage (V_{oc}), the ratio of short circuit current density to AM1.5 solar energy flux (J_{sc}/P_{solar}) and PCE of heterostructures.

Figure S1. Variations of temperature and energy against the time for AIMD simulations of the Be₂Pc monolayer.

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Figure S3. Variations of temperature and energy against the time for AIMD simulations of the Ca₂Pc monolayer.

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Figure S6. Calculated electronic band structures and corresponding total density of states (DOS) based for (a) Mg_2Pc , (b) Ca_2Pc , (c) Sr_2Pc and (d) Ba_2Pc monolayers at the PBE level. The Fermi level (E_F) is set to zero and marked with the dotted line.

Figure S7. Calculated band structures of (a) Mg₂Pc, (b) Ca₂Pc, (c) Sr₂Pc and (d) Ba₂Pc monolayers at the HSE06 level. The Fermi level is set at 0 eV.

Figure S8. The partial charge density distribution of the CBM (blue) and VBM (red) for the M₂Pc monolayers. The isosurface value is 0.003 e/Bohr³.

Figure S9. Calculated PDOS of the 2D M_2Pc monolayers in the range of -1.5 to 1.5 eV. Rows represent the PDOS contributions from different types of atoms. The last row shows TDOS for each material.

Figure S10. The evolution of PDOS on different atoms near the Fermi level versus biaxial strain from -5% to 10% for Be₂Pc monolayer. The Fermi level has been set to 0 eV.

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Figure S14. The evolution of PDOS on different atoms near the Fermi level versus biaxial strain from -5% to 10% for Ba₂Pc monolayer. The Fermi level has been set to 0 eV.

Table S1. '	The lattice	parameters (Å), space group	s and point g	roups of optimiz	ed crystal structures	s of M ₂ Pc monolayers.

M ₂ Pc	Optimized structure top (up) and side (down) views	Lattice constant	Space group	Point group
Be ₂ Pc		a = 12.34 Å b = 12.34 Å c = 15.09 Å	C2/m (#12)	C_{2h}
Mg2Pc		a = 12.48 Å b = 12.48 Å c = 15.36 Å	Cmm2 (#35)	C _{2V}
Ca2Pc		a = 12.40 Å b = 12.40 Å c = 15.53 Å	Cmm2 (#35)	C_{2V}
Sr ₂ Pc		a = 12.38 Å b = 12.38 Å c = 15.58 Å	Cmm2 (#35)	C _{2V}



Table S2. Calculated elastic constants (C_{ij} , N/m), Layer modulus (γ , N/m), Young's modulus (Y, N/m), Poisson's ratio (v) of M₂Pc nanosheets.

C tarra a tarras	C	<i>c c</i>	C	C	C		Young modulus		Poisson's ratio	
Suucluie	C_{11}	C_{22}	C_{12}	C ₆₆	γ	Y_x	Y_y	v_x	v_y	
Be ₂ Pc	71.7	70.2	24.0	18.4	47.5	63.5	62.1	0.34	0.33	
Mg ₂ Pc	57.3	56.4	21.6	16.9	39.2	49.1	48.2	0.38	0.38	
Ca ₂ Pc	44.2	44.4	22.2	15.3	33.2	33.1	33.3	0.50	0.50	
Sr ₂ Pc	40.6	41.1	21.1	14.7	30.9	29.8	30.1	0.51	0.52	
Ba ₂ Pc	38.1	38.7	20.4	14.3	29.4	27.3	27.8	0.53	0.54	

Strain	-5%	-4%	-3%	-2%	-1%	0%
Lattice	a = 14.54 Å b = 18.74 Å	a = 14.69 Å b = 18.93 Å	a = 14.85 Å b = 19.13 Å	a = 15.00 Å b = 19.33 Å	a = 15.15 Å b = 19.52 Å	a = 15.31 Å b = 19.72 Å
constant	c = 15.36 Å	c = 15.36 Å				
Mg2Pc						
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Strain	1%	2%	3%	4%	5%	
T	a = 15.46 Å	a = 15.61 Å	a = 15.76 Å	a = 15.92 Å	a = 16.07 Å	
constant	b = 19.92 Å c = 15.36 Å	b = 20.12 Å c = 15.36 Å	b = 20.31 Å c = 15.36 Å	b = 20.51 Å c = 15.36 Å	b = 20.70 Å c = 15.36 Å	
Mg ₂ Pc						
Strain	6%	7%	8%	9%	10%	
Lattice constant	a = 16.22 Å b = 20.90 Å c = 15.36 Å	a = 16.38 Å b = 21.10 Å c = 15.36 Å	a = 16.53 Å b = 21.30 Å c = 15.36 Å	a = 16.68 Å b = 21.50 Å c = 15.36 Å	a = 13.77 Å b = 17.75 Å c = 15.36 Å	
Mg ₂ Pc						

Strain	-5%	-4%	-3%	-2%	-1%	0%
T	a = 14.50 Å	a = 14.65 Å	a = 14.81 Å	a = 14.96 Å	a = 15.11 Å	a = 15.26 Å
Lattice	b = 18.57 Å	b = 18.77 Å	b = 18.97 Å	b = 19.16 Å	b = 19.36 Å	b = 19.55 Å
constant	c = 15.54 Å	c = 15.54 Å	c = 15.54 Å			
Ca ₂ Pc						
	Conce Conce			Constant of a cost of	. Constant of a constant	Consume of a grant of
Strain	1%	2%	3%	4%	5%	
Lattice	a = 15.42 Å	a = 15.57 Å	a = 15.72 Å	a = 15.87 Å	a = 16.03 Å	
constant	b = 19.75 A c = 15.54 Å	b = 19.95 A c = 15.54 Å	b = 20.14 A c = 15.54 Å	b = 20.33 A c = 15.54 Å	b = 20.53 A c = 15.54 Å	
Ca ₂ Pc	to the second of	the second se	to a constant of the second of	Terrent of the second of the s		
Strain	6%	7%	8%	9%	10%	
Lattice	a = 16.18 A b = 20.72 Å	a = 16.33 A b = 20.02 Å	a = 16.49 A b = 21.12 Å	a = 16.64 A $b = 21.21 ^{3}$	a = 16.791 A b = 21.51 Å	
constant	c = 15.54 Å	c = 15.54 Å				
Ca ₂ Pc	To a constant of the second of	To a constant of the second of	To a second of the base of the			

Strain	-5%	-4%	-3%	-2%	-1%	0%
Lattice	a = 14.49 Å	a = 14.64 Å	a = 14.79 Å	a = 14.945 Å	a = 15.10 Å	a = 15.25 Å
constant	b = 18.54 Å	b = 18.73 Å	b = 18.93 Å	b = 19.125 Å	b = 19.32 Å	b = 19.52 Å
Sr ₂ Pc						
Strain	1%	2%	3%	4%	5%	
Lattice	a = 15.40Å	a = 15.55 Å	a = 15.71 Å	a = 15.86 Å	a = 16.01 Å	
constant	b = 19.71 Å	b = 19.90 Å c = 15.58 Å	b = 20.10 Å a = 15.58 Å	b = 20.29 Å	b = 20.49 Å	
Sr ₂ Pc	To a constant of the second of	Total and the second se	To an a for the second se	To an and other and other	to an and to an and to a	
Strain	6%	7%	8%	9%	10%	
Lattice	a = 16.17 A b = 20.69 Å	a = 16.32 A b = 20.88 Å	a = 16.4 / A b = 21.08 Å	a = 16.62 A b = 21.27 Å	a = 16.77 A b = 21.46 Å	
constant	c = 15.58 Å	c = 15.58 Å	c = 15.58 Å	c = 15.58 Å	c = 15.58 Å	
Sr ₂ Pc	To a second of the barrows of the	To a more of the second of	To a succession of the success	Telescond of element of e	To a sum of the base of the	
	To a more to a more to t	To a man of o associated	Lound of our of	Toursetobasses	To aman of o base of	

Strain	-5%	-4%	-3%	-2%	-1%	0%
Lattice	a = 14.48 Å	a = 14.63 Å	a = 14.78 Å	a = 14.93 Å	a = 15.09 Å	a = 15.24 Å
constant	b = 18.49 Å	b = 18.69 Å	b = 18.88 Å	b = 19.08 Å	b = 19.27 Å	b = 19.47 Å
Ba ₂ Pc						
Strain	1%	2%	3%	4%	5%	
Lattice	a = 15.39 Å	a = 15.54 Å	a = 15.70 Å	a = 15.85 Å	a = 16.00 Å	
constant	b = 19.66 Å	b = 19.85 Å	b = 20.05 Å	b = 20.24 Å	b = 20.44 Å	
	c = 15.03 A	C = 15.05 A	C = 15.03 A	C = 15.03 A	C = 15.03 A	
Ba ₂ Pc	A C C C C C C C C C C C C C C C C C C C	A CONCERSION OF CONCERSION	A CONTRACTOR	Tolerando Tolerando	To a constant of the second of	
Strain	6%	7%	8%	9%	10%	
Lattice constant	a = 16.15 Å b = 20.63 Å c = 15.63 Å	a = 16.31 Å b = 20.83 Å c = 15.63 Å	a = 16.46 Å b = 21.02 Å c = 15.63 Å	a = 16.61 Å b = 21.22 Å c = 15.63 Å	a = 16.76 Å b = 21.41 Å c = 15.63 Å	
Ba ₂ Pc	To a constant of the second of		To a constant of the second of			





















Table S12. Computed effective mass (m^* , m_0), deformation potential constant (E_1 , eV), 2D elastic modulus (C_{2D} , N/m), and carrier mobility (μ , cm² V⁻¹ s⁻¹) of electrons and holes along x and y directions for the M_2Pc sheets at 300 K.

Structure	carrier type	m_{x}^{*}	m^*_y	E_{1x}	E_{1y}	C_{2D-x}	$C_{2\text{D-y}}$	μ_x	μ_y
Po-Do	electron	0.49	0.45	0.52	0.58	64.92	61.24	19782.18	20597.23
Be ₂ Pc	hole	4.02	2.59	4.59	1.20	64.92	61.24	8.95	23.61
MarDo	electron	0.57	0.57	1.98	1.63	54.59	56.55	1174.43	1079.76
Mg ₂ Pc	hole	3.17	1.65	1.41	1.59	54.59	56.55	70.27	144.36
Ca ₂ Pc	electron	0.55	0.44	3.54	1.61	49.45	47.65	682.49	579.20
	hole	3.69	1.37	1.70	1.97	49.45	47.65	35.95	103.12
C. D.	electron	0.56	0.45	1.91	1.55	47.19	44.94	1227.48	1369.72
Sr ₂ Pc	hole	3.17	1.21	1.64	1.89	47.19	44.94	49.51	137.94
	electron	0.57	0.48	1.91	1.56	45.58	43.04	1110.55	1193.05
Ба2Рс	hole	3.46	1.20	1.55	2.07	45.58	43.04	38.15	125.31

Table S13. Calculated band gap of the donor (E_g), conduction band offset (ΔE_c), open circuit voltage (V_{oc}), the ratio of short circuit current density to AM1.5 solar energy flux (J_{sc}/P_{solar}), and PCE of heterostructures.

Heterostructure (donor/acceptor)	$E_{g}(eV)$	$\Delta E_{\rm c}~({\rm eV})$	$V_{\rm oc}~({\rm eV})$	$J_{ m sc}/P_{ m solar}$	η
Be ₂ Pc/2H-MoSe ₂	1.21	0.05	0.86	0.422	23.61%
Mg ₂ Pc/2H-MoTe ₂	1.35	0.24	0.81	0.388	20.44%
Ca ₂ Pc/2H–WTe ₂	1.39	0.36	0.73	0.378	17.91%
Sr ₂ Pc/GaN	1.35	0.14	0.91	0.389	22.88%
Ba ₂ Pc/GaN	1.34	0.31	0.73	0.390	18.42%

Figure S1. AIMD simulations results (include the final snapshot, the evolution of total energy and temperature versus the simulation time) for the Be₂Pc monolayers at 400, 600, 800 and 1000 K, respectively.

Figure S2. AIMD simulations results (include the final snapshot, the evolution of total energy and temperature versus the simulation time) for the Mg₂Pc monolayers at 400, 600 and 800 K, respectively.

Figure S3. AIMD simulations results (include the final snapshot, the evolution of total energy and temperature versus the simulation time) for the Ca_2Pc monolayers at 400, 600 800 and 1000 K, respectively.

Figure S4. AIMD simulations results (include the final snapshot, the evolution of total energy and temperature versus the simulation time) for the Sr₂Pc monolayers at 400, 600 800 and 1000 K, respectively.

Figure S5. AIMD simulations results (include the final snapshot, the evolution of total energy and temperature versus the simulation time) for the Ba₂Pc monolayers at 400, 600 800 and 1000 K, respectively.

Figure S6. Calculated electronic band structures and corresponding total density of states (DOS) based for (a) Mg_2Pc , (b) Ca_2Pc , (c) Sr_2Pc and (d) Ba_2Pc monolayers at the PBE level. The Fermi level (E_F) is set to zero and marked with the dotted line.

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Figure S8. The partial charge density distribution of the CBM (blue) and VBM (red) for the M₂Pc monolayers. The isosurface value is 0.003 e/Bohr³.

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Figure S14. The evolution of PDOS on different atoms near the Fermi level versus biaxial strain from -5% to 10% for Ba₂Pc monolayer. The Fermi level has been set to 0 eV.